

2SK3469-01MR

FUJI POWER MOSFET

Super FAP-G Series

N-CHANNEL SILICON POWER MOSFET

Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

Maximum ratings and characteristic Absolute maximum ratings

($T_c=25^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Ratings	Unit
Drain-source voltage	V_{DS}	500	V
Continuous drain current	I_D	± 12	A
Pulsed drain current	$I_{D(puls)}$	± 48	A
Gate-source voltage	V_{GS}	± 30	V
Repetitive or non-repetitive	I_{AR}^*2	12	A
Maximum Avalanche Energy	E_{AS}^*1	217	mJ
Maximum Drain-Source dV/dt	dV_{DS}/dt	20	kV/ μs
Peak Diode Recovery dV/dt	dV/dt^*3	5	kV/ μs
Max. power dissipation	P_D	$T_a=25^\circ\text{C}$	2.16
		$T_c=25^\circ\text{C}$	50
Operating and storage temperature range	T_{ch}	+150	$^\circ\text{C}$
	T_{stg}	-55 to +150	$^\circ\text{C}$

*1 $L=2.77\text{mH}$, $V_{CC}=50\text{V}$ *2 $T_{ch}\leq 150^\circ\text{C}$ *3 $I_F\leq -I_D$, $-di/dt=50\text{A}/\mu\text{s}$, $V_{CC}\leq BV_{DSS}$, $T_{ch}\leq 150^\circ\text{C}$

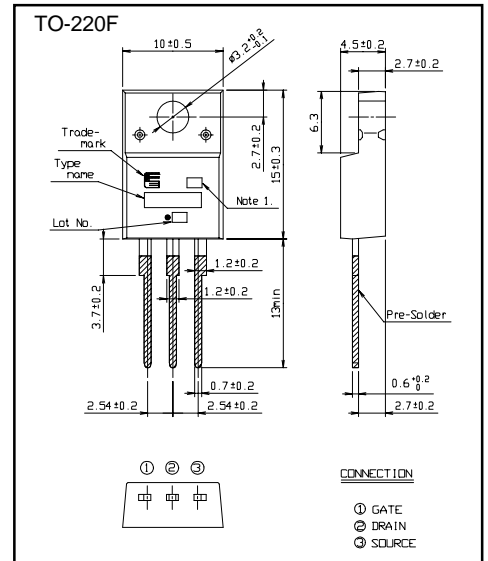
Electrical characteristics ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D=250\mu\text{A}$ $V_{GS}=0\text{V}$	500			V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250\mu\text{A}$ $V_{DS}=V_{GS}$	3.0		5.0	V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=500\text{V}$ $V_{GS}=0\text{V}$			25	μA
		$V_{DS}=400\text{V}$ $V_{GS}=0\text{V}$			250	
Gate-source leakage current	I_{GSS}	$V_{GS}=\pm 30\text{V}$ $V_{DS}=0\text{V}$		10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$I_D=6\text{A}$ $V_{GS}=10\text{V}$		0.40	0.52	Ω
Forward transconductance	g_{fs}	$I_D=6\text{A}$ $V_{DS}=25\text{V}$	5.5	11		S
Input capacitance	C_{iss}	$V_{DS}=25\text{V}$		1200	1800	pF
Output capacitance	C_{oss}	$V_{GS}=0\text{V}$		140	210	
Reverse transfer capacitance	C_{rss}	$f=1\text{MHz}$		6.0	9.0	
Turn-on time t_{on}	$t_{d(on)}$	$V_{CC}=300\text{V}$ $I_D=6\text{A}$		17	26	ns
	t_r	$V_{GS}=10\text{V}$		15	23	
Turn-off time t_{off}	$t_{d(off)}$	$R_{GS}=10\Omega$		34	51	
	t_f			7	11	
Total Gate Charge	Q_G	$V_{CC}=250\text{V}$		30	45	nC
Gate-Source Charge	Q_{GS}	$I_D=12\text{A}$		11	16.5	
Gate-Drain Charge	Q_{GD}	$V_{GS}=10\text{V}$		10	15	
Avalanche capability	I_{AV}	$L=2.77\text{mH}$ $T_{ch}=25^\circ\text{C}$	12			A
Diode forward on-voltage	V_{SD}	$I_F=12\text{A}$ $V_{GS}=0\text{V}$ $T_{ch}=25^\circ\text{C}$		1.00	1.50	V
Reverse recovery time	t_{rr}	$I_F=12\text{A}$ $V_{GS}=0\text{V}$		0.7		μs
Reverse recovery charge	Q_{rr}	$-di/dt=100\text{A}/\mu\text{s}$ $T_{ch}=25^\circ\text{C}$		4.5		μC

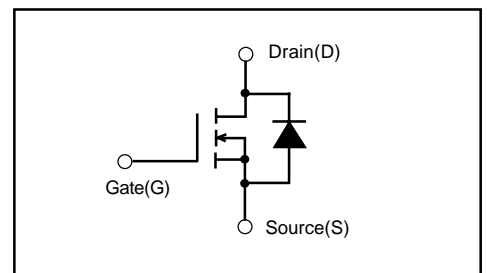
Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(ch-c)}$	channel to case			2.50	$^\circ\text{C}/\text{W}$
	$R_{th(ch-a)}$	channel to ambient			58.0	$^\circ\text{C}/\text{W}$

Outline Drawings

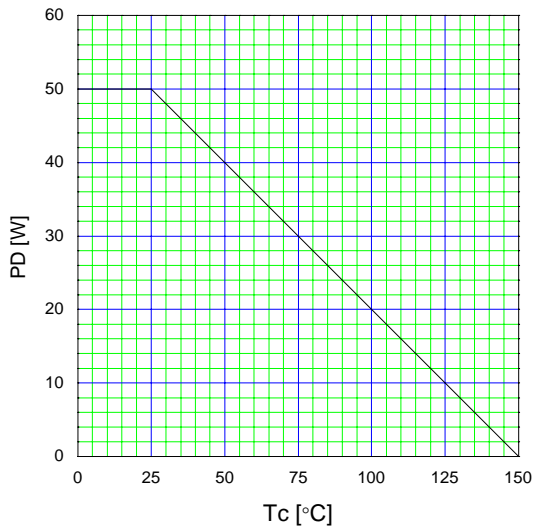


Equivalent circuit schematic

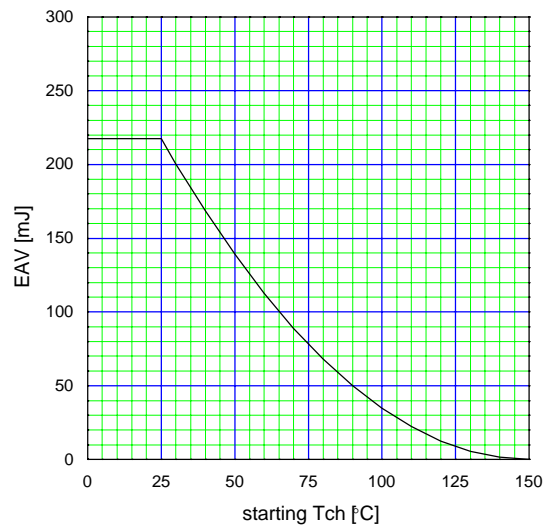


Characteristics

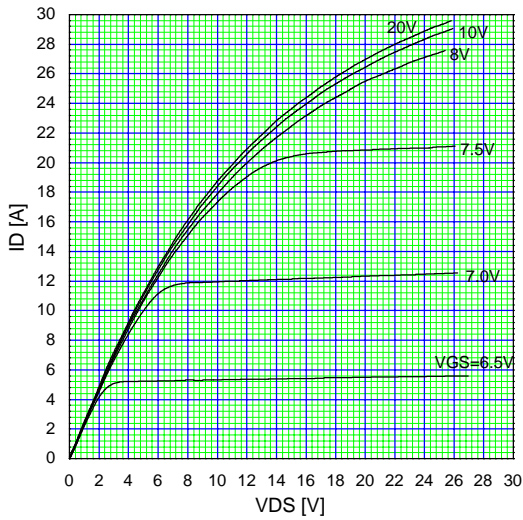
Allowable Power Dissipation
 $PD=f(T_c)$



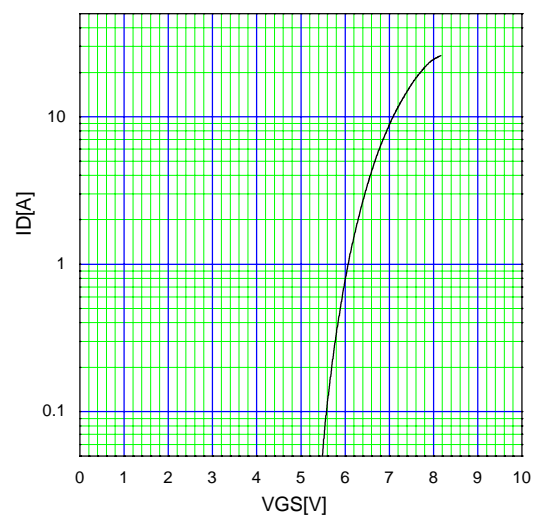
Maximum Avalanche Energy vs. starting T_{ch}
 $E(AV)=f(\text{starting } T_{ch}):V_{cc}=50V, I(AV)\leq 12A$



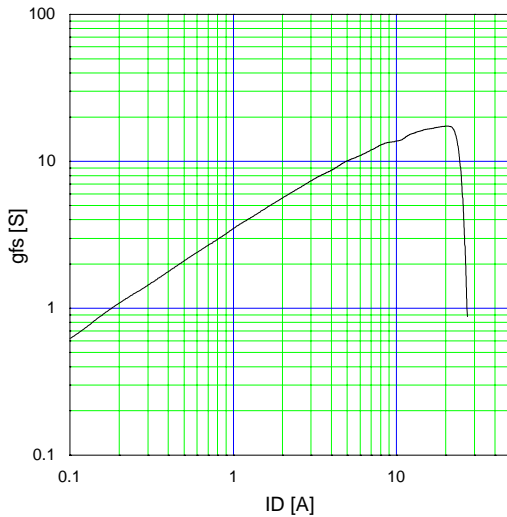
Typical Output Characteristics
 $I_D=f(V_{DS}):80\mu s \text{ Pulse test}, T_{ch}=25^\circ C$



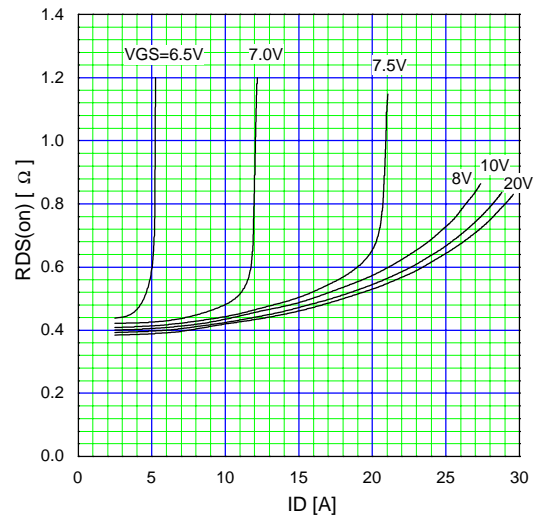
Typical Transfer Characteristic
 $I_D=f(V_{GS}):80\mu s \text{ Pulse test}, V_{DS}=25V, T_{ch}=25^\circ C$



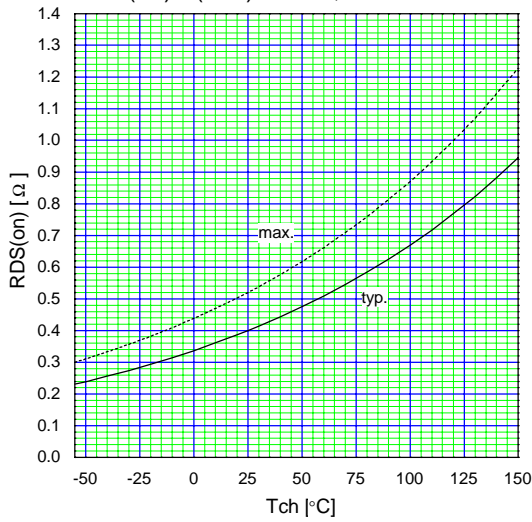
Typical Transconductance
 $g_{fs}=f(I_D):80\mu s \text{ Pulse test}, V_{DS}=25V, T_{ch}=25^\circ C$



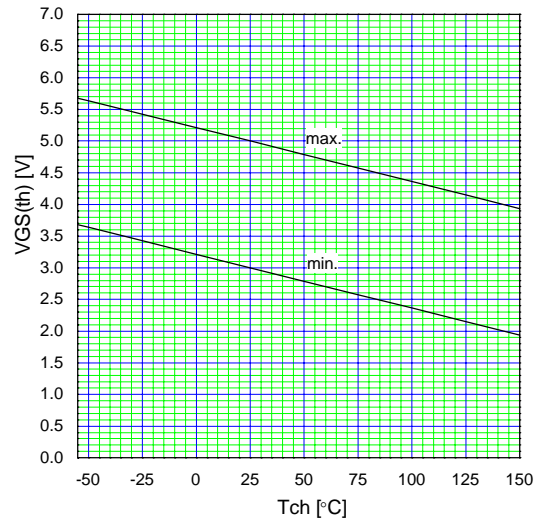
Typical Drain-Source on-state Resistance
 $R_{DS(on)}=f(I_D):80\mu s \text{ Pulse test}, T_{ch}=25^\circ C$



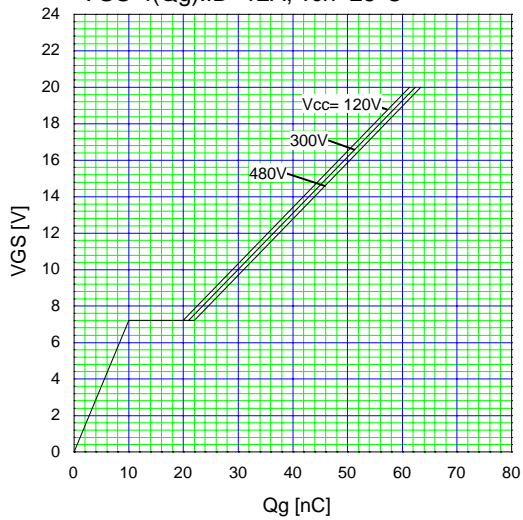
Drain-Source On-state Resistance
 $R_{DS(on)}=f(T_{ch}):I_D=6A, V_{GS}=10V$



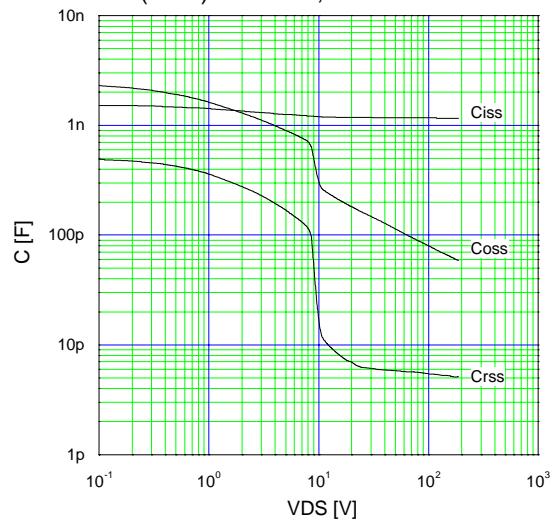
Gate Threshold Voltage vs. T_{ch}
 $V_{GS(th)}=f(T_{ch}):V_{DS}=V_{GS}, I_D=250\mu A$



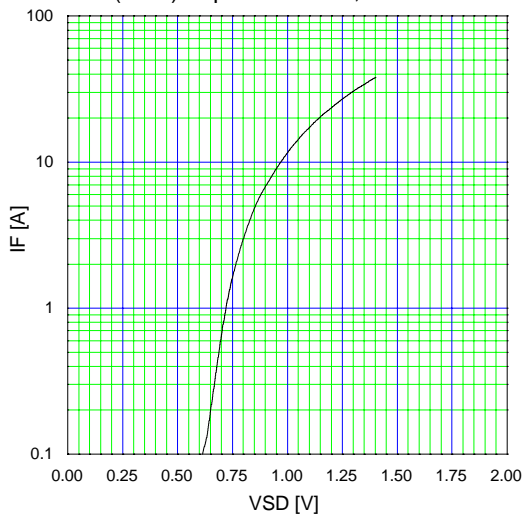
Typical Gate Charge Characteristics
 $V_{GS}=f(Q_g):I_D=12A, T_{ch}=25^{\circ}C$



Typical Capacitance
 $C=f(V_{DS}):V_{GS}=0V, f=1MHz$



Typical Forward Characteristics of Reverse Diode
 $I_F=f(V_{SD}):80\mu s$ Pulse test, $T_{ch}=25^{\circ}C$



Typical Switching Characteristics vs. I_D
 $t=f(I_D):V_{cc}=300V, V_{GS}=10V, R_G=10\Omega$

